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(54) MICRO-RESONATOR HAVING MICRO-RESONATOR HAVING (56) References Cited
LID-INTEGRATED ELECTRODE

- (12) **UNITED STATES PATENT** (10) Patent No.: US

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(54) MICRO-RESONATOR HAVING

LID-INTEGRATED ELECTRODE U.S. PATENT DOCUM

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 $H03H 3/007$ (2006.01) $H03H 3/007$
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CPC H03H 9/02259; H03H 2009/02283; H03H 9/2405; H03H 9/525; H03H 9/2463; H03H 3/0072; H03H 9/2426; B81B 2207/092; B81B 2207/095; B81B 2207/098 USPC 333 / 186 ; 257 / 415

See application file for complete search history.

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(57) ABSTRACT

A micro-resonator employs a lid-integrated electrode to one or more of drive, sense and tune a vibrational resonant mode of a microelectromechanical systems (MEMS) resonator. The micro-resonator includes a lid attached to a base that provides a resonator cavity. The micro-resonator further includes the MEMS resonator extending from a surface of the base toward the lid within the resonator cavity. The lid-integrated electrode extends vertically from the lid into the resonator cavity toward the base. The vertically extending, lid-integrated electrode is positioned spaced from and adjacent to a side of the MEMS resonator to one or more of drive, sense and tune mechanical movement of the MEMS resonator.

22 Claims, 4 Drawing Sheets

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 $FIG.$ 1B

FIG. 2A

 $FIG. 2B$

 $FIG. 3$

This application claims priority from U.S. Provisional
Patent Application Ser. No. 61/979,496, filed Apr. 14, 2014,
the entire contents of which is incorporated herein by
reference. In some embodiments, a method of micro-r

(MEMS). In particular, the invention relates to a MEMS ²⁰ micro-resonator manufacturing further comprises affixing resonator and electrodes used with the MEMS resonator resonator and electrodes used with the MEMS resonator.

2. Description of Related Art

Microelectromechanical (MEMS) resonators are micro- 25 BRIEF DESCRIPTION OF THE DRAWINGS scale mechanical solid-state resonators produced or manuscale mechanical solid-state resonators produced or manu-
factured using MEMS technology. MEMS resonators show
promise in a variety of areas including, but not limited to,
signal filtering, mass sensing, motion sensing, an references. For example, a particularly interesting potential 30 reference numerals designate like structural elements, and in application of MEMS resonators is as a vibrating structure which:
gyroscopic sensor (e.g., C gyroscopic sensor (e.g., Coriolis vibratory gyroscope) used FIG. 1A illustrates a cross sectional view of a microto determine orientation and attitude of a device or system. resonator having a lid-integrated electrode in a MEMS vibrating structure gyroscopes may hold the promise according to an embodiment consistent with the principles
of providing high precision, multi-axis, gyroscopic sensing 35 of the present invention.
using low cost dev integrated with other integrated circuit (IC) components of resonator illustrated in FIG. 1A, according to an embodi-
a system. However, while many advances have been made ment consistent with the principles of the present including, but not limited to, the use of high Q dielectric FIG. 2A illustrates a cross sectional view of a micro-
resonators, challenges still remain. Among the challenges 40 resonator including an integral mechanical ali facing MEMS resonators are providing efficient, high per-
formance and cost effective drive and sense electrodes as
mobodiment consistent with the principles of the present formance and cost effective drive and sense electrodes as embodiment consistent consistent with the principle principles of the MEMS reconstant and invention. well as providing packaging of the MEMS resonator and
electrodes that maintains or enhances the performance of FIG. 2B illustrates a cross sectional view of the micro-
these MEMS devices (e.g. performance that supports a 4 these MEMS devices (e.g., packaging that supports a 45 vacuum environment).

In some embodiments, a micro-resonator having a lid-50 example, according to an embodiment consistent with the
integrated electrode is provided. The micro-resonator com-
prises a resonator base and a resonator lid attached resonator base to provide an enclosed resonator cavity. The nator system in an example, according to an embodiment micro-resonator further comprises a microelectromechani-
consistent with the present invention. cal systems (MEMS) resonator supported by the resonator 55 FIG. 5 illustrates a flow chart of a method of micro-
base. The MEMS resonator extends from a surface of the resonator manufacturing in an example, according to an base. The MEMS resonator extends from a surface of the resonator manufacturing in an example, according to an resonator base toward the resonator lid within the resonator embodiment consistent with the present invention. cavity. The micro-resonator further comprises an electrode
integrated into the resonator lid. The lid-integrated electrode
that are one of in addition to and in lieu of the features integrated into the resonator lid. The lid-integrated electrode that are one of in addition to and in lieu of the features extends vertically from a surface of the resonator lid into the 60 illustrated in the above-referen extends vertically from a surface of the resonator lid into the 60 illustrated in the above-referenced figures. These and other resonator cavity toward the resonator base. The lid-inte-
features are detailed below with ref resonator cavity toward the resonator base. The lid-inte-
grated electrode is positioned adjacent to and spaced from a
referenced figures. vertical side of the MEMS resonator. The lid-integrated electrode is configured to one or more of drive, sense and DETAILED DESCRIPTION electrode is configured to one or more of drive, sense and tune mechanical movement of the MEMS resonator.

tune mechanical movement of the MEMS resonator.
In some embodiments, a micro-shell resonator system is In some embodiments, a micro-shell resonator system is Embodiments consistent with the principles of the present provided. The micro-shell resonator system comprises a invention provide a micro-resonator with an electrode

MICRO-RESONATOR HAVING micro-shell resonator affixed to a substrate within a resona-
LID-INTEGRATED ELECTRODE to exvity. The micro-shell resonator is configured to exhibit tor cavity. The micro-shell resonator is configured to exhibit a vibrational resonant mode. The micro-shell resonator CROSS-REFERENCE TO RELATED system further comprises an electrode integral to and $APPLICATIONS$ sextending vertically from a lid into the resonator cavity. The lid-integrated electrode is adjacent to and spaced from a sidewall of the micro-shell resonator. The lid-integrated

manufacturing is provided. The method of micro-resonator STATEMENT REGARDING FEDERALLY

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a micro-shell resonator that extends from a surface of the a micro-shell resonator that extends from a surface of the resonator base; and providing a resonator lid having elec-Background 15 trodes integral with and extending vertically from a surface of the resonator lid. The method of micro-resonator manu-1. Technical Field facturing further comprises positioning the resonator lid with the resonator base to have the surface of the resonator lid facing the surface of the resonator base. The method of The invention relates to microelectromechanical systems lid facing the surface of the resonator base. The method of
(EMS) In particular, the invention relates to a MEMS 20 micro-resonator manufacturing further comprises af micro-shell resonator in a resonator cavity formed by the positioned resonator lid and base.

tem of FIG. 2A after alignment in an example, according to an embodiment consistent with the principles of the present invention.

BRIEF SUMMARY
FIG. 3 illustrates a schematic view of interspersed drive
and sense electrodes around a micro-shell resonator in an

electrode may be integrated into a lid positioned over a the base spacer 114 are electrically isolated from one another microelectromechnical systems (MEMS) resonator (e.g., a and from the base substrate 112 by an ins microelectromechnical systems (MEMS) resonator (e.g., a and from the base substrate 112 by an insulator layer 116 of micro-shell resonator) in a vertical configuration. According the SOI wafer, for example. In some example to various embodiments, the vertical configuration of the 5 lid-integrated electrode may facilitate achieving micro-resolid-integrated electrode may facilitate achieving micro-reso-
nator (Si), silicon germanium (SiGe), or gallium
nator packaging having a compact form factor while simul-
arsenide (GaAs). Moreover, the insulator material (i. taneously accommodating a relatively large number of (i.e., insulator layer 116) of the SOI wafer may include, but is not high density) electrodes for mechanisms including, but not
limited to, silicon dioxide (Si_2O_2), silicon nitride (Si_3N_4), a
limited to, one or more of driving, sensing and tuning of the 10 dielectric polymer or a die limited to, one or more of driving, sensing and tuning of the 10 dielectric polymer or a dielectric resist material. For micro-resonator. Further according to various embodiments, example, the SOI wafer may be a silicon-on micro-resonator. Further according to various embodiments, example, the SOI wafer may be a silicon-on-insulator wafer using the vertically configured, lid-integrated electrode may that includes a layer of Si on a layer of using the vertically configured, lid-integrated electrode may that includes a layer of Si on a layer of SiO₂. The MEMS allow for enhancing, or in some embodiments, for maxi-resonator 130 is supported on the base substrat allow for enhancing, or in some embodiments, for maxi-
mizing, one or more of an applied driving force, a detection anchor or pivot 132. sensitivity, and tuning of the micro-resonator. The vertically 15 The micro-resonator 100 further comprises a micro-reso-
configured, lid-integrated electrode may facilitate both nator cap or lid 120. As illustrated in FIG configured, lid-integrated electrode may facilitate both nator cap or lid 120. As illustrated in FIG. 1A, the micro-
wafer-scale integration and chip-scale integration of the resonator lid 120 comprises a planar support 12 electrodes with the MEMS resonator, for example. More-
over, a vacuum environment surrounding the MEMS reso-
micro-resonator lid 120 may further comprise a lid spacer nator to facilitate performance (e.g., high quality or ' Q' 20 factor) may be provided, according to various embodiments.

As used herein, the article 'a' is intended to have its some embodiments, the micro-resonator lid 120 may com-
ordinary meaning in the patent arts, namely 'one or more'. prise a semiconductor-on-insulator (SOI) wafer. The ordinary meaning in the patent arts, namely 'one or more'. prise a semiconductor-on-insulator (SOI) wafer. The lid-
For example, 'an electrode' means one or more electrodes integrated electrode 140, and the lid spacer 122 and as such, 'the electrode' means 'the electrode(s)' herein. 25 vided), may be formed using wafer-scale manufacturing and Also, any reference herein to 'top', 'bottom', 'upper', chip-scale integration on the SOI wafer. Fo ' second' is not intended to be a limitation herein. Herein, the terned into the vertically extending, lid-integrated electrode term 'about' when applied to a value generally means within 140. As illustrated in FIG. 1A, th the tolerance range of the equipment used to produce the 30 another material deposited on the SOI wafer may be further value, or in some examples, means plus or minus 20%, or patterned into the lid spacer 122. The lid spac value, or in some examples, means plus or minus 20%, or plus or minus 10%, or plus or minus 1%, unless otherwise expressly specified. Further, the term 'substantially' as used herein means a majority, or almost all, or all, or an amount within a range of about 51% to about 35 100%, for example. Moreover, examples and embodiments trode 140 to be aligned with the base portion of the microherein are intended to be illustrative only and are presented resonator cavity 102 without the illustrated lid

a micro-resonator is provided. FIG. 1A illustrates a cross 40 140', and from the lid spacer 122 if provided (as illustrated sectional view of a micro-resonator 100 having a lid-
in the example in FIG. 1A), by an insulator layer 124 of the
integrated electrode in an example, according to an embodi-
SOI wafer, for example. Moreover, the lid-integ integrated electrode in an example, according to an embodi-

SOI wafer, for example. Moreover, the lid-integrated elec-

ment consistent with the principles of the present invention.

trode 140 extends vertically into the ment consistent with the principles of the present invention. trode 140 extends vertically into the micro-resonator cavity FIG. 1B illustrates a perspective view of a portion of the 102 from the micro-resonator lid 120. micro-resonator 100 illustrated in FIG. 1A in an example, 45 According to various embodiments, the micro-resonator according to an embodiment consistent with the principles lid 120 may comprise a material that is substanti according to an embodiment consistent with the principles lid 120 may comprise a material that is substantially similar of the present invention. The lid-integrated electrode is to a material of the micro-resonator base 11 configured to one or more of drive, sense and tune a
mechanical movement (e.g., a resonant vibrational mode) that includes a semiconductor such as, but not limited to, Si,

As illustrated in FIGS. 1A and 1B, the micro-resonator material. In an example, the SOI wafer of the micro-100 comprises a micro-resonator base 110 that includes a resonator lid 120 may be a silicon-on-insulator wafer that 100 comprises a micro-resonator base 110 that includes a resonator lid 120 may be a silicon-on-insulator wafer that microelectromechanical systems (MEMS) resonator 130 on includes a layer of Si and a layer of SiO₂. a base substrate 112. The base substrate 112 may be a 55 As illustrated in FIG. 1A, the MEMS resonator 130 substantially planar substrate. The micro-resonator base 110 extends from the base substrate 112 in the base portio substantially planar substrate. The micro-resonator base 110 further includes a semiconductor layer on the base substrate 112 patterned into a base spacer 114 and a base portion of a micro-resonator cavity 102. The MEMS resonator 130 is located in the micro-resonator cavity 102 at least partially 60 surrounded by the base spacer 114. In some examples, the base spacer 114 substantially surrounds the MEMS resonator 130. According to some embodiments, the micro-resotor 130. According to some embodiments, the micro-reso-
nator base 110 may be formed from a semiconductor-on-
ical sidewall of the MEMS resonator 130. In some embodinator base 110 may be formed from a semiconductor-on-
insulator (SOI) wafer. The MEMS resonator 130 and the 65 ments of the micro-resonator 100, e.g., as illustrated in insulator (SOI) wafer. The MEMS resonator 130 and the 65 ments of the micro-resonator 100, e.g., as illustrated in base spacer 114 on the base substrate 112 may be formed FIGS. 1A-1B, the MEMS resonator 130 is a micro-shel

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grated into a lid of the micro-resonator. In particular, the techniques on the SOI wafer. The MEMS resonator 130 and electrode may be integrated into a lid positioned over a the base spacer 114 are electrically isolated fr the SOI wafer, for example. In some examples, the semiconductor of the SOI wafer may include, but is not limited

resonator lid 120 comprises a planar support 126 and an micro-resonator lid 120 may further comprise a lid spacer 122 spaced from and adiacent to the lid-integrated electrode 140, for example as illustrated in FIG. 1A. According to integrated electrode 140, and the lid spacer 122 (if provided), may be formed using wafer-scale manufacturing and Also, any reference herein to 'top', 'bottom', 'upper', chip-scale integration on the SOI wafer. For example, a 'lower', 'up', 'down', 'front', back', 'left', 'right', 'first' or semiconductor layer of the micro-resonator lid 120 is pat-140. As illustrated in FIG. 1A, the semiconductor layer or another material deposited on the SOI wafer may be further least partially surround the lid-integrated electrode 140 and may form a lid portion of the micro-resonator cavity 102, in some examples. In other examples, the semiconductor layer
is patterned into the vertically extending lid-integrated elecfor discussion purposes and not by way of limitation. The lid-integrated electrode 140 is electrically isolated from
According to some embodiments of the present invention, other vertically extending lid-integrated electro

within the micro-resonator 100, according to various 50 SiGe, or GaAs; and an insulator such as, but not limited to,
embodiments. SiO_2 , Si_3N_4 , a dielectric polymer or a dielectric resist
As illustrated in FIGS. 1A an

micro-resonator cavity 102 into the base base of the micro-resonator cavity 102 . Moreover, the lid-integrated electrode 140 is positioned to vertically extend adjacent to and spaced from a vertical sidewall of the MEMS resonator 130 that extends into the base base in order the micro-resonator cavity 102. FIG. 1A illustrates the lid-integrated electrode 140 base spacer 114 on the base substrate 112 may be formed FIGS. 1A-1B, the MEMS resonator 130 is a micro-shell using wafer-scale manufacturing and MEMS fabrication resonator that is a hollow cylindrical shape having an open resonator that is a hollow cylindrical shape having an open

anchor 132 on the resonator base 110. The open end extends with electrotion to the hid portion of the micro-resonator cavity 102 . The resonator. MEMS resonator 130 may have other shapes and is further

the micro - resonator described below.

If the resonator of the resonator is the micro - resonator is the micro - resonator

If the resonator of seal 160 may have o

the micro-resonator lid 120 further comprises another lid-
integrated electrode 140 that extends from the resonator lid ured to join the micro-resonator lid 120 and the micro-

lid-integrated electrode to be an electrode pair 140, 140' that member 160 include, but are not limited to, one or more of includes the inner electrode 140' and the outer electrode 140 an adhesive, a solder, and a eutectic positioned on either side of the vertical sidewall of the According to various embodiments, the MEMS resonator $MENS$ resonator 130 , e.g., an opposing inner-outer elec-
130 may be substantially any mechanical resonator th MEMS resonator 130, e.g., an opposing inner-outer elec-
trode nair 140, 140, as described below Although not 25 configured to vibrate or move. In particular, by definition, trode pair 140, 140', as described below. Although not 25 configured to vibrate or move. In particular, by definition, illustrated, it is also within the scope of some embodiments the MEMS resonator 130 is a mechanical res herein for the micro-resonator 100 to include the lid-inte-

onlightness or vibrate within the micro-resonator

orated inner electrode 140' instead of the outer electrode cavity 102. According to some embodiments, the move grated inner electrode 140' instead of the outer electrode cavity 102. According to some embodiments, the movement
140 In FIG 1B the migre receptor lid 120 is not illus or vibration is or represents a vibrational resonator 140. In FIG. 1B, the micro-resonator lid 120 is not illus-
trated but instead is represented by a deshed outline ind: ³⁰ the MEMS resonator 130. In various examples, the MEMS trated, but instead is represented by a dashed outline indi-
cating a position of the micro-resonator lid 120 on the resonator 130 may be substantially any mechanical resonator

cal connection from the respective lid-integrated electrode

130 may be a dielectric resonator. For example, the MEMS

140, 140' to an electrically conductive contact pad 152 on an

external surface of the micro-resonator external surface of the micro-resonator lid 120. The inter- α_0 dielectric material including, but not limited to, a semicon-
connect 150 comprises the contact pad 152 comprising an ductor (e.g., silicon (Si)), an oxid connect 150 comprises the contact pad 152 comprising an ductor (e.g., silicon (Si)), an oxide (e.g., SiO₂), a nitride electrically conductive material and a via or a feed-through (e.g., Si₂N_a), a carbide (e.g., SiC) electrically conductive material and a via or a feed-through (e.g., $Si₃N₄$), a carbide (e.g., SiC), or different types of 154 filled with an electrically conductive material to provide diamond. The dielectric r 154 filled with an electrically conductive material to provide diamond. The dielectric resonator may be configured to the isolated electrical connection to the respective lid-
move or be driven by dielectric forces applied integrated electrode 140, 140'. In some examples, the elec-45 trically conductive material is also configured to provide a trically conductive material is also configured to provide a may comprise an electrically conductive material and be tight seal with the material of the micro-resonator lid 120 to configured to move or be driven by an elec tight seal with the material of the micro-resonator lid 120 to configured to move or be driven by an electric field or an support subsequent vacuum sealing of the micro-resonator electrostatic force. For example, the MEMS support subsequent vacuum sealing of the micro-resonator electrostatic force. For example, the MEMS resonator 130 cavity 102. For example, the materials may have one or both may be constructed from a conductive metal, a do cavity 102. For example, the materials may have one or both may be constructed from a conductive metal, a doped
of compatible thermal expansion coefficients and compat- 50 semiconductor (e.g., doped Si), or a dielectric ma ible lattice matching to accommodate any physical stresses $SiO₂$) that is coated with an electrically conductive material on the sealed micro-resonator 100. The electrically conduc-
such as, but not limited to, a la on the sealed micro-resonator 100. The electrically conduc-
tive materials for the contact pad 152 and the via 154 another example, the MEMS resonator 130 may comprise a tive materials for the contact pad 152 and the via 154 another example, the MEMS resonator 130 may comprise a independently include, but are not limited to, one or more of magnetic material and therefore be a magnetic reso polysilicon, doped polysilicon, another doped semiconduc- 55 tor material, and a conductive metal.

fabricated during wafer-scale manufacturing of the micro-
resonator lid 120 and using chip-scale integration to provide
externally accessible integral interconnections to the respec- 60 130 is a substantially non-planar or externally accessible integral interconnections to the respec- 60 130 is a substantially non-planar or three-dimensional (3D) tive lid-integrated electrodes 140, 140'. In some examples, structure having a height (or ver tive lid-integrated electrodes 140, 140'. In some examples, structure having a height (or vertical dimension), a length the location of the interconnect 150 through the micro-
and a depth, or having a height (i.e., vertica the location of the interconnect 150 through the micro-
resonator lid 120 and its position relative to the respective a diameter or a circumference. For example, the shape of the lid-integrated electrode 140 , $140'$ provide a shorter path MEMS resonator 130 may include, but is not limited to, a length (i.e., through the thickness of the resonator lid). As 65 hemispherical shape, a cylindrical such, the interconnect 150 may have less parasitic capaci-
tance and impedance of the conduction path, for example
pendently may include, but are not limited to, substantially

end opposite to an end thereof that is supported by the relative to a separate drive-sense device or a tuning device anchor 132 on the resonator base 110. The open end extends with electrodes attached to a resonator substr

100 further comprises an attachment member or seal 160 located between the micro-resonator lid 120 and the micro-Further, as illustrated in FIG. 1A, in some embodiments, located between the micro-resonator lid 120 and the micro-
e micro-resonator lid 120 further comprises another lid. resonator base 110. The attachment member 160 is integrated electrode 140' that extends from the resonator lid ured to join the micro-resonator no 120 and the micro-
120 verticelly into the lid portion of the micro resonator essenator base 110 together such that the micr 120 vertically into the lid portion of the micro-resonator resonator base 110 together such that the micro-resonator resonator $\frac{10}{10}$ cavity 102 is fully enclosed. In some embodiments, the cavity 102. In these embodiments, the other lid-integrated ¹⁰ cavity 102 is fully enclosed. In some embodiments, the electrode 140' is internally positioned adjacent to and spaced attachment member 160 is a layer of att electrode 140' is internally positioned adjacent to and spaced
from the vertical sidewall of the MEMS resonator 130 and
may be opposite to the externally positioned lid-integrated
electrode 140. The internal-positioned or facturing, for example, and using wafer materials of the MEMS resonator 130 from an external environment. Sealing
micro-resonator lid 120.
It is within the scope of some embodiments for the 20 Examples of attachment materi

cating a position of the micro-resonator lid 120 on the
resonator 130 may be substantially any mechanical resona-
resonator base 110 of the micro-resonator 100.
According to various embodiments, the micro-resonator
lid 120

move or be driven by dielectric forces applied to the MEMS resonator 130. In other examples, the MEMS resonator 130 magnetic material and therefore be a magnetic resonator configured to move or be driven by a magnetic field or tor material, and a conductive metal.

In some embodiments, the interconnect 150 may be may be a piezoelectric resonator comprising a piezoelectric

> a diameter or a circumference. For example, the shape of the MEMS resonator 130 may include, but is not limited to, a pendently may include, but are not limited to, substantially

but not exceed an overall height of the micro-resonator MEMS resonator 130 may be hollow, solid (e.g., a solid dielectric micro-shell structure.

disk), or partially hollow or partially solid and may be closed According to some embodiments, the micro-shell resona-

at opposite at opposite ends, open at one end and closed at an opposite tor 130 is formed using MEMS fabrication techniques and
base end (adjacent to the anchor 132), or open at one end and 5 wafer-scale manufacturing techniques using have spokes extending between a central hub and the walls As mentioned above, the micro-resonator base 110 and the of the resonator structure at the opposite base end. As such, micro-resonator lid 120 also may be formed us of the resonator structure at the opposite base end. As such, micro-resonator lid 120 also may be formed using wafer-
the MEMS resonator 130 has a vertically extending side or scale manufacturing techniques and chip-scale the MEMS resonator 130 has a vertically extending side or
sidewall between the opposite ends thereof, by definition In some embodiments, the micro-shell resonator 130 as well
herein. In some embodiments, the vertical heigh herein. In some embodiments, the vertical height of the 10 MEMS resonator 130, including a sidewall height and a MEMS resonator 130, including a sidewall height and a micro-shell structures described in co-pending U.S. Patent height of the anchor 132, exceeds a height of the base Application of Deborah J. Kirby, et al., "A Dielectric portion of the micro-resonator cavity 102, as illustrated in Q MEMS Shell Gyroscope structure," application Ser. No.
FIGS. 1A-1B. In particular, the height of the MEMS reso-
nator 130, including the anchor 132 height, is s extend into the lid portion of the micro-resonator cavity 102, resonator 130 and the micro-resonator lid 120 with the adjacent to the respective lid-integrated electrode 140, 140' may be but not exceed an overall height of the micro-resonator assembled into the micro-resonator 100 using wafer bonding
cavity 102.
In other embodiments (not illustrated), the vertical height 20 In some embodiments, one or both

of the MEMS resonator 130, including a sidewall height and outer electrode 140 and the lid-integrated inner electrode a height of the anchor 132, is less than a height of the base 140' is configured to one or both of drive a height of the anchor 132, is less than a height of the base 140' is configured to one or both of drive and sense a portion of the micro-resonator cavity 102. In particular, the mechanical movement (e.g., vibrational reso portion of the micro-resonator cavity 102. In particular, the mechanical movement (e.g., vibrational resonator mode) of height of the MEMS resonator 130, including the anchor 132 the MEMS resonator 130. In some embodiments height, does not exceed the combined height (thickness) of 25 the insulator layer 116 and the base spacer layer 114 of the configured to tune the MEMS resonator 130, e.g., to com-
micro-resonator base 110. In some of these embodiments, pensate for any asymmetry of the MEMS resonator micro-resonator base 110. In some of these embodiments, pensate for any asymmetry of the MEMS resonator 130. For the respective lid-integrated electrode 140, 140' extends example, the respective lid-integrated electrode 14 within the base portion of the micro-resonator cavity 102 may be biased to achieve mode matching wherein a mode adjacent to the sidewall of the MEMS resonator 130. These 30 frequency is adjusted or the MEMS resonator 130 i adjacent to the sidewall of the MEMS resonator 130. These 30 frequence embodiments include eliminating the lid spacer 122 and damped. embodiments include eliminating the lid spacer 122 and contacting the base spacer 114 with the micro-resonator lid As described above, the MEMS resonator 130 extends 120 (e.g., the lid insulator layer 124) by way of the attach-

from the substrate portion of the micro-resonato 120 (e.g., the lid insulator layer 124) by way of the attachment member 160, for example.

In some examples, the vertical height of the sidewalls of 35 the MEMS resonator 130 may be greater than about one electrode 140, 140' is configured to extend vertically from fourth $(\frac{1}{4})$ of the width or diameter of the MEMS resonator the micro-resonator lid 120 toward the micro fourth (4) of the width or diameter of the MEMS resonator the micro-resonator lid 120 toward the micro-resonator base
130, for example. In other examples, the vertical height of 110 in the micro-resonator cavity 102 adj 130, for example. In other examples, the vertical height of 110 in the micro-resonator cavity 102 adjacent to the MEMS the sidewalls may be greater than about one third $\langle \frac{1}{2} \rangle$ of the resonator 130. For example, the MEMS resonator width or diameter, or greater than about 40 one half $(\frac{1}{2})$ of the MEMS resonator width or diameter, or one half $(\frac{1}{2})$ of the MEMS resonator width or diameter, or cavity 102 externally adjacent to the side of the MEMS greater than the MEMS resonator width or diameter. resonator 130 (i.e., the outer electrode 140). In so

In some embodiments (e.g., as illustrated in FIGS. 1A-1B), the MEMS resonator 130 comprises a micro-shell 1A-1B), the MEMS resonator 130 comprises a micro-shell to vertically extend in the micro-resonator cavity 102, but resonator 130. By definition herein, a 'micro-shell' resonator 45 extends internally adjacent to the side o resonator 130. By definition herein, a 'micro-shell' resonator 45 extends internally adjacent to the side of the MEMS resonator 130 that comprises a substantially nator 130 (i.e., the inner electrode 140'). As such, in add hollow structure with a relatively thin sidewall, e.g., a sidewall that is thin relative to other dimensions of the hollow structure. The substantially hollow micro-shell reso-
the micro-resonator lid 120 a sufficient vertical distance into nator 130 may include, but is not limited to, a sphere, a 50 the micro-resonator cavity 102 to be positioned spaced from half-sphere, other spheroids, other half spheroids, a closed and vertically adjacent to the MEMS reso half-sphere, other spheroids, other half spheroids, a closed and vertically adjacent to the MEMS resonator vertical side evaluation of the MEMS resonator vertically adjacent to the MEMS resonator vertical side of the metal example, FIGS. 1A-1B illustrate the hollow micro-shell FIG. 1A illustrates both the vertical extension of each of resonator 130 having a substantially cylindrical shape. In the respective lid-integrated electrodes 140, 140 particular, the cylindrically shaped, micro-shell resonator 55 micro-resonator lid 120 and the vertical side-adjacent,
130 illustrated in FIGS. 1A-1B has an open end oriented spaced positioning of the respective lid-integr toward the micro-resonator lid 120. Further, as illustrated in 140, 140' next to the MEMS resonator 130. The vertical FIG. 1A, the cylindrically shaped, micro-shell resonator 130 extension and the side-adjacent, spaced pos FIG. 1A, the cylindrically shaped, micro-shell resonator 130 extension and the side-adjacent, spaced positioning of the is attached by the anchor 132 to the resonator substrate 112 respective lid-integrated electrodes 140, at the base end, which is at least partially closed. Vibrational 60 trol of one or both of drive and sense mechanical movement
resonator modes of the cylindrically shaped, micro-shell of the MEMS resonator 130, according t resonator modes of the cylindrically shaped, micro-shell resonator 130 may include, but are not limited to, a so-called resonator 130 may include, but are not limited to, a so-called ments. In some examples, the position and the spacing of the view-

"wine-glass" mode, for example. In some examples, the respective lid-integrated electrodes 'wine-glass' mode, for example. In some examples, the respective lid-integrated electrodes 140, 140' further facili-
micro-shell resonator 130 comprises a dielectric micro-shell tate tuning of the MEMs resonator 130 to com resonator that is configured to be driven by dielectric forces 65 from an electric gradient. In other examples, the micro-shell

straight walls or substantially tapered walls. Further, the as, but not limited to, a conductive metal coating on the MEMS resonator 130 may be hollow, solid (e.g., a solid dielectric micro-shell structure.

Application of Deborah J. Kirby, et al., "A Dielectric High respective lid-integrated electrode 140, 140 may be

the MEMS resonator 130. In some embodiments, one or both of the respective lid-integrated electrodes 140, 140' is example, the respective lid-integrated electrode 140, 140'

and in some examples, into the lid portion of the micro-resonator cavity 102. Further, the respective lid-integrated resonator 130. For example, the lid-integrated electrode 140 is positioned to vertically extend in the micro-resonator resonator 130 (i.e., the outer electrode 140). In some examples, the lid-integrated electrode $140'$ is also positioned nator 130 (i.e., the inner electrode $140'$). As such, in addition to being integrated with the micro-resonator lid 120, the respective lid-integrated electrode 140, 140' protrudes from

the respective lid-integrated electrodes 140, 140' from the respective lid-integrated electrodes 140, 140' facilitate control of one or both of drive and sense mechanical movement tate tuning of the MEMs resonator 130 to compensate for any asymmetry of the MEMs resonator 130. The lid-integrated outer electrode 140 is distinguished from substanresonator 130 further comprises a conductive material such tially planar or 'surface' electrodes (i.e., for any of drive,

lid-integrated outer electrode 140 is distinguished from one
or both a drive-sense device and a tuning device having integrated electrode 140 and the inner lid-integrated elecor both a drive-sense device and a tuning device having integrated electrode 140 and the inner lid-integrated electrodes that is attached adjacent to a $\frac{1}{2}$ trode 140' may be a member of a plurality of the respective other configurations as well and may have additional features.

In some examples, a distance or gap between the respective lid-integrated electrode 140, 140' and the MEMS resotive lid-integrated electrode 140, 140' and the MEMS reso-
nabodiments, the plurality of the respective lid-integrated
nator sidewall may be made relatively small and further, the
electrode 140, 140' or the plurality of op gap distance may be precisely controlled by using electrodes electrode pairs 140 , $140'$ may be distributed along or around integrated into the micro-resonator 140 , as described 15 the MEMS resonator 130 . For exampl integrated into the micro-resonator lid 120, as described 15 according to the principles herein. A precisely controlled gap according to the principles herein. A precisely controlled gap 100 may have a plurality of lid-integrated inner-outer elec-
distance may enhance, and in some examples, may maxi-
trode pairs 140, 140' distributed around a p mize one or more of a drive force, a sensing sensitivity and micro-shell resonator 130 (e.g., around a periphery of the a tuning capability between the respective lid-integrated open-ended cylinder). A first set of opposin a tuning capability between the respective lid-integrated open-ended cylinder). A first set of opposing inner-outer electrode 140, 140' and the MEMS resonator 130. In con- 20 electrode pairs 140, 140' of the respective plu electrode 140, 140' and the MEMS resonator 130. In con- 20 electrode pairs 140, 140' of the respective plurality may be trast, it may be difficult to one or both of achieve and control configured as drive electrodes. A sec the relatively small spacing between a drive electrode, a inner-outer electrode pairs 140, 140' of the respective plusense electrode or a tuning electrode and a resonator when rality may be configured as sense electrodes. sense electrode or a tuning electrode and a resonator when rality may be configured as sense electrodes. Moreover, a
the electrodes are surface electrodes located above or below third set of opposing inner-outer electrode the resonator on one or both of the lid and the substrate, for 25 the respective plural example. Further, it may be difficult to control of the trodes, for example. positioning and the gap distance of electrodes attached on a According to some examples, the first and second sets of separate drive and sense device or a tuning device along a opposing inner-outer electrode pairs 140, 140 separate drive and sense device or a tuning device along a opposing inner-outer electrode pairs 140, 140' may be alter-
side of the resonator. The respective lid-integrated elec-
nated around the MEMS resonator 130. For ex trodes 140, 140' described herein may substantially over- 30 come these difficulties and other difficulties in manufactur-
ing a micro-resonator. According to various embodiments apart from one another around the interior and exterior ing a micro-resonator. According to various embodiments apart from one another around the interior and exterior herein, the respective lid-integrated electrode 140, 140' is periphery of the micro-shell resonator 130. Simil herein, the respective lid-integrated electrode 140, 140' is periphery of the micro-shell resonator 130. Similarly, four configured to generate one or more of an electric gradient opposing inner-outer electrode pairs 140, force, an electrostatic force and a bias voltage on the MEMS 35 resonator 130. Moreover, the respective lid-integrated elecresonator 130. Moreover, the respective lid-integrated elec-
trole another around the interior and exterior periphery of the
trode 140, 140' is configured to sense a capacitance change
micro-shell resonator 130. In this ex with respect to the MEMS resonator 130 moving in an sense electrode pairs of the second set also may be inter-
electric field, for example.
In the spersed around the micro-shell resonator 130 at about forty-

the micro-resonator lid 120. For example, the electrode may interspersed drive and sense electrodes 140, 140' around a comprise a doped semiconductor of the semiconductor micro-shell resonator 130 in an example, according comprise a doped semiconductor of the semiconductor micro-shell resonator 130 in an example, according to an device layer of the SOI wafer of the micro-resonator lid 120. embodiment consistent with the present invention. T The respective lid-integrated electrode 140 , $140'$ is made 45 and sense electrodes 140 , $140'$ accessible external to the micro-resonator 100 by way of the labeled 'D' and 'S', respectively. accessible external to the micro-resonator 100 by way of the labeled 'D' and 'S', respectively.
above-described circuitry (e.g., the interconnect 150) inte-
In some embodiments (not illustrated in FIG. 3), the third above-described circuitry (e.g., the interconnect 150) inte-
grated into the micro-resonator lid 120, according to some or tuning set of opposing inner-outer electrode pairs 140,

integrated electrodes 140, 140' may be configured as inner opposing inner-outer electrode pairs 140, 140' of the third or and outer electrode pairs 140, 140' to one or both of drive tuning set may be positioned about ninet and outer electrode pairs 140, 140' to one or both of drive tuning set may be positioned about ninety degrees (90°) and sense the MEMS resonator movement in a push-pull apart from one another around the interior and exteri and sense the MEMS resonator movement in a push-pull apart from one another around the interior and exterior relationship. For example, to drive movement of the micro-
periphery of the micro-shell resonator 130. Further, t shell resonator 130 in a push-pull relationship, a voltage 55 respective tuning electrode pairs of the third set also may be applied to an inner electrode 140' may be ninety degrees interspersed around the micro-shell reso applied to an inner electrode $140'$ may be ninety degrees (90°) out of phase to a voltage applied to an opposing outer electrode 140. Using a push-pull relationship for one or both of driving movement and sensing movement may reduce, or Moreover, it is within the scope of some embodiments for
in some examples may minimize, the voltage applied to 60 one or more of the drive ('D') electrodes or electro in some examples may minimize, the voltage applied to ω drive the micro-shell resonator 130. Moreover, using a drive the micro-shell resonator 130. Moreover, using a or one or more of the sense ('S') electrodes or electrode pairs push-pull relationship for one or both of driving movement of the opposing inner-outer electrodes 140, push-pull relationship for one or both of driving movement of the opposing inner-outer electrodes 140, 140 'illustrated in and sensing movement may increase, or in some examples FIG. 3 to be configured as tuning electrodes and sensing movement may increase, or in some examples FIG. 3 to be configured as tuning electrodes or tuning may maximize, a sensitivity to movement of the micro-shell electrode pairs instead of drive or sense electrodes resonator 130, according to various embodiments. In some 65 Alternatively, any of the respective electrodes in the first and examples, the pair of opposing inner and outer lid-integrated second sets may be configured to pr

sense and tune mechanisms) above or below a resonator on measurements, for example to achieve common-mode noise
one or both of a lid and a resonator substrate. Moreover, the rejection and reduction of parasitic capacitance

side-positioned electrodes that is attached adjacent to a 5 trode 140 may be a member of a plurality of the respective resonator on a resonator substrate. Embodiments of the electrode, or the opposing inner and outer lid-i resonator on a resonator substrate. Embodiments of the electrode, or the opposing inner and outer lid-integrated micro-resonator 100 that instead or in addition include the electrode pair 140, 140' may be a member of a plu micro-resonator 100 that instead or in addition include the electrode pair 140, 140' may be a member of a plurality of lid-integrated inner electrode 140' distinguishes from these such inner-outer lid-integrated electrode such inner-outer lid-integrated electrode pairs. FIG. 1A illustrates two inner electrodes 140' and two outer electrodes 10 140 respectively positioned on either side of the illustrated micro-shell resonator 130, by way of example. In some electrode 140 , $140'$ or the plurality of opposing inner-outer electrode pairs 140 , $140'$ may be distributed along or around distance may enhance, and in some examples, may maxi-
mize one or more of a drive force, a sensing sensitivity and
micro-shell resonator 130 (e.g., around a periphery of the third set of opposing inner-outer electrode pairs 140, 140 of the respective plurality may be configured as tuning elec-

nated around the MEMS resonator 130. For example, four opposing inner-outer electrode pairs 140, 140' in the first (or opposing inner-outer electrode pairs 140 , $140'$ in the second (or 'sense') set also may be positioned about 90° apart from micro-shell resonator 130. In this example, the respective sense electrode pairs of the second set also may be inter-According to some embodiments, the respective lid- 40 five degrees (45°) from the respective drive electrode pairs
integrated electrode 140, 140' may comprise a material of of the first set. FIG. 3 illustrates a schematic embodiment consistent with the present invention. The drive and sense electrodes 140, 140' illustrated in FIG. 3 are

embodiments.
In some embodiments, opposing inner and outer lid- $\frac{140}{140}$ may be interspersed with one or both of the drive
In some embodiments, opposing inner and outer lid- $\frac{140}{140}$ and the sense electrode sets. In some embodiments, opposing inner and outer lid- so electrode sets and the sense electrode sets. For example, four integrated electrodes 140, 140' may be configured as inner opposing inner-outer electrode pairs 140, 140' periphery of the micro-shell resonator 130. Further, the respective tuning electrode pairs of the third set also may be twenty-two degrees (22°) from the electrode pairs of the first set or the second set.

examples, the pair of opposing inner and outer lid-integrated second sets may be configured to provide tuning in addition electrodes 140, 140' may allow for differential capacitance to driving or sensing, and still be with to driving or sensing, and still be within the scope of the principles described herein. For example, in some embodi-
ments, either the first set or the second set of opposing a stable bond area for affixing the micro-resonator lid 120 ments, either the first set or the second set of opposing a stable bond area for affixing the micro-resonator lid 120 inner-outer electrode pairs 140, 140' may be configured to and the micro-resonator base 110 together. In provide both drive and sense mechanisms, while the other of examples, the respective spacers 114, 122 further facilitate the first and second sets of opposing inner-outer electrode 5 wafer bonding between the micro-resonat the first and second sets of opposing inner-outer electrode $\overline{5}$ pairs 140, 140' may be configured to provide tuning.

trode pairs 140, 140' described above may include one or the external environment, for example. A bond or seal 160
both of other drive and sense electrode sets 140, 140' and (i.e., using the attachment member 160) between both of other drive and sense electrode sets 140, 140' and (i.e., using the attachment member 160) between the respecture electrode sets 140, 140', for example. In other embodi- 10 tive spacers 114, 122 is illustrated in F tune electrode sets 140, 140', for example. In other embodi- 10 tive spacers 114, 122 is illustrated in FIGS. 1A-1B, by way ments (not illustrated), the plurality of lid-integrated elec-
of example and not limitation. trodes may be limited to alternating drive electrodes, sense In some embodiments, the micro-resonator cavity 102 is electrodes and tuning electrodes positioned either external configured to be hermetically sealed using the electrodes and tuning electrodes positioned either external (electrodes 140) to the micro-shell resonator or internal member 160. In some embodiments, the hermetically sealed (electrodes 140) to the micro-shell resonator. Moreover, it is 15 micro-resonator cavity 102 may be within the scope of the principles herein for a plurality of the vacuum encapsulation of the MEMS resonator 130. Vacuum lid-integrated electrodes to be respectively vertically posi-

lid-integrated electrodes to be respect lid-integrated electrodes to be respectively vertically positioned side-adjacent to a MEMS resonator that is other than tioned side-adjacent to a MEMS resonator that is other than ciated with a resonance of the MEMS resonator 130, for evindrical in shape.

electrode. In particular, one or both of the lid-integrated an integral mechanical alignment system. FIG. 2A illustrates electrodes 140, 140' may be configured to provide an electric a cross sectional view of a micro-reson electrodes 140, 140' may be configured to provide an electric a cross sectional view of a micro-resonator 100 including an gradient force to drive a dielectric MEMS resonator 130 integral mechanical alignment system 170 in (e.g., a dielectric micro-shell resonator 130) using dielectric 25 according to an embodiment consistent with the principles forces. Similarly, one or both of the lid-integrated electrodes of the present invention. FIG. 2B 140, 140' may be configured to sense motion of the dielectric view of the micro-resonator 100 including the integral MEMS resonator 130 (e.g., a dielectric micro-shell resona-
mechanical alignment system 170 of FIG. 2A in tor 130) using an electric gradient force sense mode. An electric gradient force electrode may comprise a pair of 30 principles of the present invention. In particular, FIG. 2A adjacent lid-integrated electrodes (either adjacent outer elec-
trodes 140 or adjacent inner electrodes 140') and an applied prior to bonding of the micro-resonator lid 120 and the trodes 140 or adjacent inner electrodes 140') and an applied prior to bonding of the micro-resonator lid 120 and the alternating current (AC) voltage configured to produce an micro-resonator base 110, while FIG. 2B illustr alternating current (AC) voltage configured to produce an micro-resonator base 110, while FIG. 2B illustrates the cross
AC electric field between the adjacent electrodes. In some sectional view after alignment and bonding, examples, the adjacent lid-integrated electrodes are mem- 35

trodes and the use of electric gradient force to drive and mechanical alignment between the micro-resonator base 110 sense motion in a dielectric MEMS resonator is provided by and the micro-resonator lid 120 during assembl sense motion in a dielectric MEMS resonator is provided by and the micro-resonator lid 120 during assembly (e.g., for co-pending U.S. Patent Application Publication No. 2015/40 wafer bonding). The provided active mechanica 0000401 \AA 1 to Perahia et al., and Perahia et al., "Electric is configured to establish a relative position of the respective gradient force drive mechanism for novel micro-scale all-
lid-integrated electrode 140, 140 dielectric gyroscope," 2014 IEEE $27th$ Int. Conf. on Micro Electro Mechanical Systems (MEMS), 26-30 Jan. 2014, pp. 721-724, both of which are incorporated herein in their 45 entirety. In other examples, another electrode configuration may be employed such as when the MEMS resonator 130 adjacent to the exterior side of the micro-shell resonator 130 (e.g., a metal micro-shell resonator 130) is configured to be and positioning the inner lid-integrated elec (e.g., a metal micro-shell resonator 130) is configured to be and positioning the inner lid-integrated electrode 140' adja-
one or both of driven and sensed using capacitive electric cent to the interior side of the microone or both of driven and sensed using capacitive electric cent to the interior side of the micro-shell resonator. In the fields, for example.

50 embodiments that include the opposing outer and inner

resonator base 110 and the micro-resonator lid 120 including provided by the integral mechanical alignment system 170 the above-described respective spacers 114, 122, either the enables simultaneous positioning of the oppo micro-resonator base 110 or the micro-resonator lid 120 may
include a spacer at least to facilitate delineation of the 55 Further, the provided active mechanical alignment may
micro-resonator cavity 102 and still be within resonator 100 is configured to support the combined height tive inner electrode 140' and the respective outer electrode of the MEMS resonator 130 and the anchor 132 without 60 140 of the opposing lid-integrated electrode p of the MEMS resonator 130 and the anchor 132 without ω 140 of the opposing lid-integrated electrode pair as well as making physical contact with the micro-resonator lid 120. The cavity height provided by the respective spacer is electrodes 140 , $140'$ and the sidewall of the micro-shell sufficient to support an unencumbered combined height of resonator 130 may be relatively tight to facilitate drive and the MEMS resonator 130 and the anchor 132 in the micro-
sense coupling between the respective lid-integ resonator 100. In some examples, the spacer may be fabri-65 cated as a separate part that is subsequently affixed to one or cated as a separate part that is subsequently affixed to one or over, assembly of the micro-resonator lid 120 and the both the micro-resonator base 110 and the micro-resonator micro-resonator base 110 together for bonding

and the micro-resonator base 110 together. In some irs 140, 140' may be configured to provide tuning . micro-resonator base 110. The respective spacers 114, 122
Other respective sets of the plurality of inner-outer elec- may facilitate sealing the micro-resonator cavity 10 Other respective sets of the plurality of inner-outer elec-
trole pairs 140, 140' described above may include one or
the external environment, for example. A bond or seal 160

In some embodiments, one or both of the lid-integrated 20 According to some embodiments of the principles electrodes 140, 140' comprises an electric gradient force described herein, the micro-resonator 100 further comprise of the present invention. FIG. 2B illustrates a cross sectional mechanical alignment system 170 of FIG. 2A in another example, according to an embodiment consistent with the sectional view after alignment and bonding, by way of example.

bers of a set of interdigital electrodes.
Additional description of electric gradient force electric eral alignment system 170 is configured to provide active
trodes and the use of electric gradient force to drive and
mech lid-integrated electrode 140, 140' with respect to MEMS resonator 130 in the micro-resonator cavity 102. For example, the active mechanical alignment provided by the integral mechanical alignment system 170 enables one or both of positioning of the outer lid-integrated electrode 140 fields, for example.
In some embodiments, instead of both of the micro-
lectrode pair 140, 140', the active mechanical alignment
dignment enables simultaneous positioning of the opposing lid-inte-

> resonator 130. For example, a spacing between the respecthe gap distances between the respective inner and outer sense coupling between the respective lid-integrated electrodes 140, 140' and the micro-shell resonator 130. Moremicro-resonator base 110 together for bonding may prevent

140' and the micro-shell resonator 130 (i.e., it may be a blind lattice mismatch to the first material sufficient to provide the assembly). The integral mechanical alignment system 170 is stress of the out-of-plane flex of assembly). The integral mechanical alignment system 170 is stress of the out-of-plane flex of the pre-loaded beam. The configured to provide active mechanical alignment during mismatch stress may be sufficient to achieve t configured to provide active mechanical alignment during mismatch stress may be sufficient to achieve the out-of-
assembly including positioning the respective lid-integrated 5 plane height to the alignment key 171 that ex electrodes 140, 140' relative to the micro-shell resonator 130 combined height of the MEMS resonator 130 and the anchor that, in some examples, has substantially precise control of 132 (i.e., an alignment key clearance hei

In some embodiments, the integral mechanical alignment 10 system 170 comprises an alignment key 171 at an end of a system 170 comprises an alignment key 171 at an end of a materials used to form the MEMS resonator 130 and the cantilevered, pre-loaded beam and a corresponding align-
base spacer 114). One or both of the silicon and the i cantilevered, pre-loaded beam and a corresponding align-
meat notich 172 configured to receive the alignment key 171, material may be materials of a base SOI wafer. Moreover, as illustrated in FIGS. 2A and 2B. By definition, the 'pre-
loaded' beam is configured to provide an out-of-plane flex to 15 surface coated with a eutectic material, for example during loaded' beam is configured to provide an out-of-plane flex to 15 the cantilevered beam relative to a plane of the microthe cantilevered beam relative to a plane of the micro-
the application of a eutectic alloy material of the attachment
resonator lid 120 and a plane of the micro-resonator base
member or seal 160 on the base spacer 114 of resonator lid 120 and a plane of the micro-resonator base member or seal 160 on the base spacer 114 of the micro-
110, as illustrated in FIG. 2A. The out-of-plane flex of the resonator base 110. Additionally, although not cantilevered beam is configured to facilitate the active the mechanical alignment system 170 may be fabricated mechanical alignment during assembly of the micro-reso- 20 during wafer-scale manufacturing using MEMS techniqu nator 100. In particular, the out-of-plane flex of the canti-
levered above, but located along edges of the respective
levered beam positions the alignment key 171 to a height
micro-resonator lid and base wafers, i.e., out that is greater than the combined height of the MEMS 160 of the micro-resonator 100, and still facilitate the resonator 130 and the anchor 132 on the micro-resonator alignment described herein. base 110 in some examples. The out-of-plane flex of the 25 Other alignment arrangements and techniques may be cantilevered beam is configured to enable engagement used that are within the scope of the principles described
between the alignment key 171 and the corresponding herein. For example, a pre-loaded beam having the alignalignment notch 172 prior to the point during assembly of ment key may be located on the micro-resonator lid 120 and
the micro-resonator base 110 and the micro-resonator lid the corresponding alignment notch may be located 120 when the lid-integrated electrodes 140, 140' and the 30 micro-resonator base 110. Moreover, in some examples, micro-shell resonator 130 are positioned side-adjacent to alternating alignment keys and corresponding align one another. Moreover, once the alignment key 171 is notches may be present on each of the micro-resonator lidengaged in the alignment notch 172, the mechanical align-
120 and the micro-resonator base 110. In other example engaged in the alignment notch 172, the mechanical align - 120 and the micro-resonator base 110. In other examples, the ment is to substantially control precise positioning of the pre-loaded beam alignment key may have a h lid-integrated electrodes 140, 140' with respect to the 35 MEMS resonator 130 as the micro-resonator lid 120 and the MEMS resonator 130 and its anchor 132, and the integral micro-resonator base 110 are mated together for bonding. mechanical alignment system 170 may further include

Further, by 'active' mechanical alignment, it is meant that another means for ensuring engagement of the alignment the pre-loaded beam is compressed (e.g., like a spring) into key in the corresponding alignment notch befor the respective plane of the micro-resonator base 110 and the 40 resonator lid 120 and the micro-resonator base 110 make micro-resonator lid 120 when the micro-resonator base and contact during assembly. In some examples, t lid 110, 120 are mated together during alignment or assem-
bly, for example, to be sealed together as illustrated in FIG. within the resonator lid as well as the integral mechanical
2B. Further, 'active' mechanical alignme mean that surface tension between a surface of the alignment 45 resonator form factor reduction. The form factor reduction key 171 and a surface of the alignment notch 172 facilitates may facilitate reduced manufacturing c key 171 and a surface of the alignment notch 172 facilitates may facilitate reduced manufacturing costs, in particular, alignment of the micro-resonator base 110 and the micro-
resonator id 120. In some embodiments, the su one or both of the alignment key 171 and the corresponding According to some embodiments of the present invention, alignment notch 172 may be functionalized to facilitate 50 a micro-shell resonator system is provided. FIG. surface attraction or enhance surface energy of the respec-
tive surfaces. In the embodiment illustrated in FIGS. 2A-2B, example, according to an embodiment consistent with the tive surfaces. In the embodiment illustrated in FIGS. 2A-2B, example, according to an embodiment consistent with the the pre-loaded beam alignment key 171 is integrally formed present invention. As illustrated, the micro-s the pre-loaded beam alignment key 171 is integrally formed present invention. As illustrated, the micro-shell resonator on the micro-resonator base 110 and the corresponding system 200 comprises a micro-shell resonator 210 alignment notch 172 is integrally formed in the micro- 55 resonator lid 120, by way of example and not limitation resonator lid 120, by way of example and not limitation affixed to a substrate 212. For example, the micro-shell
resonator 210 may be affixed to the substrate 212 at or by a

semiconductor or an oxide). For example, the materials of 60 the micro-resonator base 110 used to form the base spacer the micro-resonator base 110 used to form the base spacer formed by the substrate 212 and the lid 222 encloses the 114 or the MEMS resonator 130 may be used to form the micro-shell resonator 210. 114 cantilevered beam. Moreover, the pre-loaded beam of the According to some embodiments, the micro-shell resona-
114 alignment key 171 may be formed during wafer-scale manu-
10 may be substantially similar to the micro-s facturing of the base SOI wafer using MEMS techniques, for 65 example. To obtain the out-of-plane flex, in some examples, at least a surface of the cantilevered beam may be coated

using visual observation of the lid-integrated electrodes 140, with a second material that has a thermal mismatch or a 140' and the micro-shell resonator 130 (i.e., it may be a blind lattice mismatch to the first material plane height to the alignment key 171 that exceeds the

the respective gaps therebetween to substantially avoid For example, the cantilevered beam may be made from damage, for example.
silicon (the first material) that is cantilevered from an silicon (the first material) that is cantilevered from an insulator pivot material (e.g., substantially similar to the

the corresponding alignment notch may be located on the pre-loaded beam alignment key may have a height that is substantially the same height as the combined height of the icro-resonator base 110 are mated together for bonding. The mechanical alignment system 170 may further include
Further, by 'active' mechanical alignment, it is meant that another means for ensuring engagement of the align key in the corresponding alignment notch before the micro-resonator lid 120 and the micro-resonator base 110 make alignment system described herein will facilitate a micro-
resonator form factor reduction. The form factor reduction

system 200 comprises a micro-shell resonator 210. According to various embodiments, the micro-shell resonator 210 is resonator 210 may be affixed to the substrate 212 at or by a
According to some embodiments, the pre-loaded beam of support. The micro-shell resonator 210 is configured to According to some embodiments, the pre-loaded beam of support. The micro-shell resonator 210 is configured to the alignment key 171 may comprise a first material (e.g., a exhibit a vibrational resonant mode. The micro-shel exhibit a vibrational resonant mode. The micro-shell resonator system 200 further comprises a lid 222. A cavity

> tor 210 may be substantially similar to the micro-shell resonator 130 described above with respect to the microresonator 100. For example, the micro-shell resonator 210 may be a dielectric micro-shell resonator comprising a

dielectric hollow cylinder having a closed first end and an some embodiments, the seal may facilitate maintaining a open second end. Further, the support may affix the dielec-
vacuum (or at least a substantial vacuum) with tric cylinder to the substrate 212 at the closed first end, while According to some embodiments, the spacer may be subtrate open second end faces away from the substrate 212, for stantially similar to one or both of the sp

electrode 220 and an inner electrode 220 integral to and above with restending vertically from the lid 222 into the cavity (i.e., embodiments. towards the substrate 212). The lid 222 further comprises 10 In addition, the micro-shell resonator system 200 may integral interconnection circuitry to provide electrical con-
In the comprise a mechanical alignment system integral interconnection circuitry to provide electrical connection from an exterior surface of the lid 222 to the respective lid-integrated electrodes 220, 220'. According to mechanical alignment between the substrate 212 and the lid various embodiments, the outer electrode 220 is positioned 222 during assembly. In particular, the provided mechanical adjacent to and spaced from an outer surface of the micro-15 alignment is configured to establish a rel adjacent to and spaced from an outer surface of the micro-15 shell resonator 210. The inner electrode 220' extends from shell resonator 210. The inner electrode 220' extends from or both of the outer electrode 220 and the inner electrode the lid 220 adjacent to and spaced from an inner surface of 220' with respect to micro-shell resonator 2 the micro-shell resonator 210, according to various embodi-
ments. In some examples, the outer and inner electrodes 220,
220, ment system is substantially similar to the integral mechani-
220' comprise respective pairs of outer and inner electrodes 220, 220' are configured to one or described above. In particular, the mechanical alignment more of drive, sense and tune the vibrational resonant mode system may comprise an alignment key on an end of a
of the micro-shell resonator 210, as illustrated in FIG. 4 by cantilevered, pre-loaded beam integral with one of the micro-shell resonator 210, as illustrated in FIG. 4 by cantilevered, pre-loaded beam integral with one of the double-headed arrows.

According to some embodiments, the outer electrode 220 25 notch integral with a respective other of the substrate 212 may be substantially similar to the outer lid-integrated and the lid 222. The alignment notch is configu may be substantially similar to the outer lid-integrated and the lid 222. The alignment notch is configured to accept electrode 140 of the micro-resonator 100, described above. or engage with the alignment key. The pre-loa electrode 140 of the micro-resonator 100, described above. or engage with the alignment key. The pre-loaded beam is Similarly, the inner electrode 220' may be substantially configured to provide an out-of-plane flex relati Similarly, the inner electrode 220' may be substantially configured to provide an out-of-plane flex relative to the similar to the inner lid-integrated electrode 140', described plane of the substrate 212 and the lid 222. above with respect to the micro-resonator 100, according to 30 some embodiments. In some embodiments, the interconnec-
tion circuitry is substantially similar to the interconnect 150
described above with respect to the micro-resonator 100.
Moreover, the respective pairs of electrodes be substantially similar to the opposing inner-outer lid- 35 integrated electrode pair 140, 140', described above with provide a drive voltage to one or both of the outer electrode respect to the micro-resonator 100, according to some 220 and the inner electrode 220'. The drive volt respect to the micro-resonator 100, according to some $\overline{220}$ and the inner electrode 220'. The drive voltage may be embodiments. For example, the outer electrode 220 and the an alternating current (AC) voltage, for ex embodiments. For example, the outer electrode 220 and the an alternating current (AC) voltage, for example. In some inner electrode 220' in combination may be configured to embodiments that include both inner and outer ele inner electrode $220'$ in combination may be configured to embodiments that include both inner and outer electrodes both drive and sense the vibrational resonant mode in a 40 220 , $220'$, a phase of the drive voltage pr both drive and sense the vibrational resonant mode in a 40 220, 220', a phase of the drive voltage provided to the inner push-pull arrangement using voltages applied by way of the electrode 220' may be about ninety degree interconnection circuitry to the respective electrodes 220 , $220'$. Further, the outer electrode 220 and the inner electrode 220'. Further, the outer electrode 220 and the inner electrode 220. The drive voltages being 90° out of phase with one 220' in combination may be configured to drive and sense another may be employed when the inner a the vibrational resonant mode according to or using electric 45 gradient forces. Electric gradient forces may be used to one gradient forces. Electric gradient forces may be used to one vibrational resonant mode in a push-pull relationship, for or both of drive and sense the vibrational resonant mode example. In some embodiments, the power suppl or both of drive and sense the vibrational resonant mode example. In some embodiments, the power supply 230 is
when the micro-shell resonator 210 is a dielectric micro-
further configured to provide a bias voltage to one o shell resonator, for example. Moreover, one or both of the the inner and outer electrodes 220, 220' to tune the micro-
inner electrode 220' and the outer electrode 220 may be a 50 shell resonator 210. The power supply 230 inner electrode $220'$ and the outer electrode 220 may be a 50 tuning electrode.

resonator system 200, the lid 222 and the substrate 212 are
mated together for assembly to enclose the micro-shell a method of micro-resonator manufacturing is provided.
resonator 210 within the resonator cavity. As such, combination of the substrate 212 and the lid 222 is a housing resonator manufacturing in an example, according to an or enclosure for the micro-shell resonator 210. In some embodiment consistent with the present invention. embodiments, the lid 222, the substrate 212 and the micro-
shell resonator 210 and their assembly are substantially facturing comprises providing 310 a resonator base having shell resonator 210 and their assembly are substantially facturing comprises providing 310 a resonator base having
similar to the various embodiments and examples of the 60 a micro-shell resonator extending from a surface similar to the various embodiments and examples of the 60 a micro-shell resonator extending from a surface of the micro-resonator 100, described above.

For example, the micro-shell resonator system 200 may base having a micro-shell resonator is substantially similar further comprises a spacer between the lid 222 and the to the micro-resonator base 110 and the MEMS resonat further comprises a spacer between the lid 222 and the to the micro-resonator base 110 and the MEMS resonator substrate 212. The spacer facilitates formation of the cavity 130 described above with respect to the micro-reso substrate 212. The spacer facilitates formation of the cavity 130 described above with respect to the micro-resonator that accommodates the micro-shell resonator 210. The 65 100. spacer may include a bonding layer to provide a seal In some embodiments, the resonator base having the between the lid 220 and the substrate 212, for example. In micro-shell resonator is provided 310 using SOI wafer-scale

example, toward the lid 222.

S described above with respect to the micro-resonator 100.

According to various embodiments, the micro-shell reso-

Moreover, the bonding layer or seal may be substantially

nator system 200 similar to the attachment member or seal 160, described above with respect to the micro-resonator 100, in some

mechanical alignment system is configured to provide active

plane of the substrate 212 and the lid 222. An engagement of the alignment key in the alignment notch is configured to

 200 may further comprise a power supply 230 , according to some embodiments. The power supply 230 is configured to electrode $220'$ may be about ninety degrees (90°) out of phase with the drive voltage provided to the outer electrode another may be employed when the inner and outer electrodes 220, 220' are configured to one of drive and sense the further configured to provide a bias voltage to one or both of hing electrode.
According to various embodiments of the micro-shell provide the voltages to the respective electrodes 220, 220'.

embodiment consistent with the present invention. As illusicro-resonator 100, described above.
For example, the micro-shell resonator system 200 may base having a micro-shell resonator is substantially similar

micro-shell resonator is provided 310 using SOI wafer-scale

manufacturing techniques, MEMS fabrication techniques adjacent to outer edges of the respective SOI wafers may and chip-scale integration techniques. For example, a spacer reduce any misalignment between the resonator base layer of about 250 microns thick is added to an SOI wafer resonator lid caused by theta rotation of the respective base
and is patterned with a cavity. The micro-shell resonator is and lid wafers during subsequent assembly patterned in the formed cavity from a dielectric mold of 5 examples, the fabricated mechanical alignment system on about 350 microns thick, for example. The patterned spacer the resonator base and the resonator lid is subs about 350 microns thick, for example. The patterned spacer layer is to provide both a stable bond area and to maintain layer is to provide both a stable bond area and to maintain same as the active mechanical alignment system 170 a targeted height with respect to the micro-shell resonator described above for the micro-resonator 100. height for later bonding with a resonator lid. FIG. 2A In some examples, a backside substrate or layer of the lid
illustrates an example of the resonator base provided 310 10 SOI wafer (opposite side to the formed electrod illustrates an example of the resonator base provided 310 10 SOI wafer (opposite side to the formed electrodes) may be according to the method 300 of micro-resonator manufac-
thinned (i.e., 'wafer thinning' for example usi

alignment system may be located within or adjacent to the age and further, to create the interconnection circuitry, such cavity and fabricated at the time of the fabrication of the 15 as a via or feed-through, in the lid S cavity and fabricated at the time of the fabrication of the 15 micro-shell resonator, for example. An example of the micro-shell resonator, for example. An example of the lower loss. Wafer thinning may also facilitate electrochemi-
portions of an integral mechanical alignment system is cal deposition of metals into the via that may enhan portions of an integral mechanical alignment system is cal deposition of metals into the via that may enhance
illustrated in FIG. 2A-2B with respect to the integral filled-via integrity, for example, when vacuum sealing is illustrated in FIG. 2A-2B with respect to the integral filled-via integrity, for example, when vacuum sealing is mechanical alignment system 170. Moreover, a seal ring used for the assembled micro-resonator package. may be applied to a surface of the spacer surrounding the 20 In some examples, the via is formed through the lid SOI cavity to facilitate sealing to a resonator lid. As described wafer using the same Bosch process mentione above for the integral alignment system 170, a metal mate-

Moreover, the lid SOI wafer may receive a thermal oxidation

rial of the seal ring may also be applied to the cantilevered

to create both a passivation and a pr beam at the time the seal ring is applied. In some examples, the formed electrode and via before filling the via with the metal material on the cantilevered beam is to stress the 25 electrically conductive material, in som the metal material on the cantilevered beam is to stress the 25 electrically conductive material, in some examples. The via
beam to facilitate a pre-loaded beam having an out-of-plane may be filled from the wafer backside

ther comprises providing 320 a resonator lid having an and electrically access the via. In some examples, another electrode and interconnection circuitry integrated into the 30 ring of bonding or sealing material may be applied adjacent resonator lid. In some examples, the electrode is substan-
tially similar to the respective lid-integrated electrode 140, the integrally formed electrode extend from (i.e., opposite to tially similar to the respective lid-integrated electrode 140, the integrally formed electrode extend from (i.e., opposite to 140' described above with respect to the micro-resonator the backside). In some examples, the bo 140' described above with respect to the micro-resonator the backside). In some examples, the bonding ring material 100. For example, one or both of an inner electrode and an is located on the lid spacer and is intended to outer electrode are fabricated to extend vertically from a 35 surface of the lid, and be spaced apart from one another if surface of the lid, and be spaced apart from one another if illustrates an example of the resonator lid provided 320 both are present to accommodate a thickness of the resonator according to the method 300 of micro-resonat both are present to accommodate a thickness of the resonator according to the method 300 of micro-resonator manufac-
sidewall (e.g., opposing inner-outer electrodes of the lid-
turing. integrated electrode pair 140, 140'). Moreover, in some The method 300 of micro-resonator manufacturing furexamples, the interconnection circuitry may be substantially 40 ther comprises positioning 330 the resonator lid with the similar to the interconnect 150 described above with respect resonator base such that the lid-integrated electrode extends to the micro-spell resonator 100.

using one or more of SOI wafer-scale manufacturing tech-
niques, MEMS fabrication techniques and chip-scale inte-45 according to the method 300 of micro-resonator manufacniques, MEMS fabrication techniques and chip-scale inte- 45 according to the method 300 of micro-resonator manufacgration techniques on an SOI wafer. In some examples, the turning. electrode may be formed from a semiconductor device layer As illustrated in FIG. 5 by way of example, the method of the SOI wafer. For example, the electrode is etched from 300 of micro-resonator manufacturing may further of the SOI wafer. For example, the electrode is etched from 300 of micro-resonator manufacturing may further comprise a silicon device layer using a dry anisotropic silicon etch engaging 340 an integral mechanical alignmen based on a Bosch process to form vertical, highly doped 50 align the resonator base to the resonator lid. In some silicon electrode structure in the lid SOI wafer. examples, engaging 340 the integral mechanical alignment

layer may be patterned into a lid spacer that surrounds the key in an alignment notch, wherein the alignment key may electrode and forms a lid cavity. In other examples, the lid be integral to one of the resonator base and spacer is not included. The lid spacer may have a height that 55 is about the same as the vertical extent of the formed is about the same as the vertical extent of the formed be alternatively integrated in a respective other one of the electrode, for example. In some examples, another portion of resonator lid and the resonator base or the r electrode, for example. In some examples, another portion of resonator lid and the resonator base or the respective wafer
the active mechanical alignment system corresponding to thereof. Further, engaging 340 the integral the resonator base alignment system portion is also patterned ment system also closely positions opposing inner and outer and may be formed in the lid spacer, for example, adjacent 60 electrodes of a lid-integrated electro and may be formed in the lid spacer, for example, adjacent 60 electrodes of a lid-int to the lid cavity. The same process sequence as used for the micro-shell resonator. electrode may be employed, for example. In other examples,
the some examples, the mechanical alignment system
the alignment system portions of the base and the lid may be
patterned outside the cavity and the seal area nea patterned outside the cavity and the seal area near an edge of the lid-integrated electrode with respect to the micro-shell
of the lid SOI wafer and the base SOI wafer using wafer-65 resonator. For example, depending on th of the lid SOI wafer and the base SOI wafer using wafer- 65 resonator. For example, depending on the embodiment, one scale manufacturing, MEMS techniques and chip-scale inte- or both of the outer electrode and the inner el scale manufacturing, MEMS techniques and chip-scale inte-

or both of the outer electrode and the inner electrode is

gration. The placement of the alignment system portions

respectively positioned spaced from and adjace

reduce any misalignment between the resonator base and the and lid wafers during subsequent assembly together. In some examples, the fabricated mechanical alignment system on

according to the method 300 of micro-resonator manufac-
thinned (i.e., 'wafer thinning' for example using a form of
chemical mechanical polishing) to decrease an overall the chanical mechanical polishing) to decrease an overall
In some embodiments, a portion of an integral mechanical height of a subsequently assembled micro-resonator pack-

to create both a passivation and a protect layer of $SiO₂$ over the formed electrode and via before filling the via with flex with respect to the plane of the resonator base. conductive material. Further, a probe or contact pad may be
The method 300 of micro-resonator manufacturing fur-
formed on the wafer backside surface, for example to ca is located on the lid spacer and is intended to align with the seal ring on the base spacer described above. FIG. 2A further

the micro-resonator 100.
In some embodiments, the resonator lid is provided 320 base in the cavity. FIG. 2A further illustrates an example of In some embodiments, the resonator lid is provided 320 base in the cavity. FIG. 2A further illustrates an example of using one or more of SOI wafer-scale manufacturing tech-
positioning 330 the resonator lid with the reson

engaging 340 an integral mechanical alignment system to align the resonator base to the resonator lid. In some In some examples, an outer edge of the silicon device system comprises engaging an active mechanical alignment Inver may be patterned into a lid spacer that surrounds the system an alignment notch, wherein the alignment ke be integral to one of the resonator base and the resonator lid or the respective wafer thereof and the alignment notch may thereof. Further, engaging 340 the integral mechanical align-

respectively positioned spaced from and adjacent to an

exterior side of the micro-shell resonator and positioned resonator enclosed in a resonator cavity between a resonator spaced from adjacent to an interior side of the micro-shell lid having a vertically configured, integra resonator with respective predetermined gap distances the resonator base. It should be understood that the aboveebetween. Moreover, alignment accuracies of less than a few described examples are merely illustrative of some of the microns may substantially avoid damage to the micro-shell s many specific examples and embodiments that microns may substantially avoid damage to the micro-shell 5 many specific examples and embodiments that represent the resonator and reduce bias offsets when gap spacing between principles consistent with the principles des the respective electrode and the micro-shell resonator differ Clearly, those skilled in the art can readily devise numerous from one side of the micro-shell to the other side. In contrast, other arrangements without depart wafer aligners typically have accuracies no better than ten sistent with the principles described herein as defined by the microns to several microns. A misalignment in one direction 10 following claims. by one micron would translate to a two-micron difference in What is claimed is:
gap spacing between the respective electrode and the micro-
1. A micro-resonator having a lid-integrated electrode gap spacing between the respective electrode and the micro-

1. A micro-

1. A micro-

and resonator sidewalls, for example. The integral active comprising: shell resonator sidewalls, for example. The integral active comprising:
mechanical alignment system described herein may facili-
a resonator base; mechanical alignment system described herein may facili-
tate a pre-alignment accuracy of the respective lid-integrated 15 a resonator lid attached to the resonator base to provide an tate a pre-alignment accuracy of the respective lid-integrated 15 a resonator lid attached to the electrode or opposing inner-outer electrode pair with the enclosed resonator cavity; electrode or opposing inner-outer electrode pair with the enclosed resonator cavity;
micro-shell resonator that is better than tens of microns and a microelectromechanical systems (MEMS) resonator micro-shell resonator that is better than tens of microns and more like about one micron, in some examples.

In some examples, the out-of-plane flex of the alignment resonator base toward resonator cavity; and we resonate resonator cavity; and key pre-loaded beam may provide the engagement 340 of 20 resonator cavity; and
the mechanical alignment key in the alignment notch at a an electrode integrated into the resonator lid, the lidthe mechanical alignment key in the alignment notch at a separation distance between the resonator lid and the resoseparation distance between the resonator lid and the resonator integrated electrode extending vertically from a surface
nator base that is greater than a combined height that the of the resonator lid into the resonator ca micro-shell resonator extends above the resonator base resonator base and that the respective inner and outer electrodes 25 resonator cavity, extend from the surface of the lid to avoid contact between wherein the lid-integrated electrode is positioned adjacent
the electrodes and the micro-shell resonator. In particular, to and spaced from a vertical side of the the resonator lid and the resonator base may be achieved to one or more of drive, sense and tune a mechanical during assembly before the respective electrodes are pre- 30 movement of the MEMS resonator. during assembly before the respective electrodes are pre- 30 movement of the MEMS resonator.

cisely aligned with the micro-shell resonator, according to 2. The micro-resonator of claim 1, wherein the MEMS

some embodiment alignment key in the alignment notch may prevent damage end opposite an end supported by the resonator base, the to one or both of the micro-shell resonator and the electrodes vertical side of the MEMS resonator being one

trated in FIG. 5 further comprises affixing 350 together the 3. The micro-resonator of claim 2, further comprising positioned resonator lid and resonator base to enclose the another electrode integrated into the lid, the o positioned resonator lid and resonator base to enclose the another electrode integrated into the lid, the other lid-
micro-shell resonator in a resonator cavity formed by the integrated electrode vertically extending from resonator lid and base. In some embodiments, the positioned 40 resonator lid and resonator base are aligned by engaging 340 resonator lid and resonator base are aligned by engaging 340 lid-integrated electrode being positioned adjacent to and
the integral mechanical alignment system, as described spaced from the vertical side of the micro-shell the integral mechanical alignment system, as described spaced from the vertical side of the micro-shell resonator
herein, before the resonator lid and base are affixed 350 opposite the lid-integrated electrode, wherein the herein, before the resonator lid and base are affixed 350 opposite the lid-integrated electrode, wherein the lid-inte-
together. In some embodiments, affixing 350 the resonator grated electrodes form an inner-outer electro lid and the resonator base together may comprise forming a 45 ured to one or both of drive and sense hermetic seal to support vacuum encapsulation of the micro-
movement in a push-pull relationship. hermetic seal to support vacuum encapsulation of the micro - movement in a pull resonator of claim 2, wherein the micro-formed by a eutectic bond, for example, wherein the applied shell resonator comprises a dielectric mic formed by a eutectic bond, for example, wherein the applied shell resonator comprises a dielectric micro-shell resonator seal ring is a eutectic alloy material. In some examples, having a shape that is substantially cylind wafer bonding is used to affix 350 the resonator lid and base 50 5. The micro-resonator of claim 1, wherein the lid-
together. In some embodiments, affixing 350 the resonator integrated electrode is an electric gradient fo together. In some embodiments, affixing 350 the resonator integrated electrode is an electric gradient force electrode lid and the resonator base together includes bonding together configured to provide an electric gradien the seal or bonding ring on the spacers on one or both of the MEMS resonator using dielectric forces.

resonator lid and the resonator base, for example. In some **6.** The micro-resonator of claim 1, further comprising a resonator lid and the resonator base, for example. In some **6**. The micro-resonator of claim 1, further comprising a embodiments, the spacers further facilitate formation of the 55 spacer having a seal ring between the res embodiments, the spacers further facilitate formation of the 55 resonator cavity that houses the micro-shell resonator. FIG. resonator cavity that houses the micro-shell resonator. FIG. resonator base, wherein the resonator cavity is configured to 2B illustrates an example of the affixed resonator lid and be hermetically sealed at an interface b resonator base of the micro-resonator manufactured accord-
ing to the resonator lid and the
ing to the method 300, for example. The lid-integrated
resonator base. electrodes are aligned with the micro-shell resonator in the 60 7. The micro-resonator of claim 6, wherein the hermeti-
resonator cavity by the method 300 herein in a configuration cally sealed resonator cavity is confi resonator cavity by the method 300 herein in a configuration cally sealed resonator cavity is configured to provide
to perform one or more of driving, sensing and tuning the vacuum encapsulation of the MEMS resonator to fa to perform one or more of driving, sensing and tuning the vacuum encapsulation of the MEMS resonator to facilitate vibrational resonant mode of the micro-shell resonator, for the mechanical movement associated with a reson vibrational resonant mode of the micro-shell resonator, for the mechanical movement associated with a resonance mode example.

Thus, there have been described examples of a micro- 65 8. The micro-resonator of claim 1, further comprising a resonator, a micro-shell resonator system and a method of mechanical alignment system integral to and configur resonator, a micro-shell resonator system and a method of mechanical alignment system integral to and configured to manufacturing a micro-resonator that provide a MEMS provide active mechanical alignment between the resona

lid having a vertically configured, integrated electrode and a other arrangements without departing from the scope con-

-
-
- supported by and extending from a surface of the resonator base toward the resonator lid within the
- of the resonator lid into the resonator cavity toward the resonator base and spaced from a sidewall of the
-

during assembly.
The method 300 of micro-resonator manufacturing illus-
micro-shell resonator.

integrated electrode vertically extending from the lid surface
into the resonator cavity toward the resonator base, the other grated electrodes form an inner-outer electrode pair configured to one or both of drive and sense the MEMS resonator

configured to provide an electric gradient to drive the MEMS resonator using dielectric forces.

be hermetically sealed at an interface between the spacer

provide active mechanical alignment between the resonator

from adjacent position of the lid-integrated electrode with alignment key on a pre-loaded beam integral with one of the
respect to the vertical side of the MEMS resonator substrate and the lid and a corresponding alignment

mechanical alignment system comprises an alignment key the pre-roaded beam having an out-or-plane flex relative to a plane of one or both of the substrate and the lid, wherein on a pre-loaded beam integral with one of the resonator base
and the alignment key is engaged with the alignment integral and the resonator lid and a corresponding alignment notch
the resonator base a substantially paralle and the resonator lid and a corresponding alignment notch the pre-loaded beam has a substantially parallel flex to the integral with a respective other of the resonator base and the substantially parallel flex to the integ integral with a respective other of the resonator base and the plane of one or both of the substrate and the lid.

resonator lid, the pre-loaded beam having an out-of-plane ¹⁰ **18**. A method of micro-resonator manufactur flex relative to a plane of the resonator lid or the resonator method comprising:
base to facilitate engagement of the alignment key with the providing a resonator base having a micro-shell resonator base to facilitate engagement of the alignment key with the providing a resonator base having a micro-shell resonator base;
alignment het providing a resonator base having a micro-shell resonator base; alignment notch, the active mechanical alignment between that extends from a surface of the resonator base;
the resonator base and the resonator lid comprising both the providing a resonator lid having electrodes integral the resonator base and the resonator lid comprising both the 15 providing a resonator lid having electrodes integral with a proporcion a surface of the resonator comprision and extending vertically from a surface of the re engagement of the alignment key with the alignment notch and extending vertically from a surface of the resonance of the and the pre-loaded beam flexed into the plane of the reso-

- a micro-shell resonator affixed to a substrate within a $_{20}$ of the resonator base; and a resonator base in a diffixing together the positioned resonator lid and resonation assembly contained a resonator base $_{20}$
- an electrode integral to and extending vertically from a lid resonator cavity formed by the resonator nanufacturing of ...
19. The method of micro-resonator manufacturing of

the ind-integrated electrode comprises both an outer elec-
trode exterior to the micro-shell resonator sidewall and an
opposing inner electrodes being configured to perform one or
opposing inner electrodes positioned inter shell resonator sidewall, in combination the outer and inner according to an electric gradient force.

20. The method of micro-resonator manufacturing of electrodes are configured to one or both of drive and sense 20. The method of micro-resonator manufacturing of
the vibrational resonator made in a nuclearly number of claim 18, wherein affixing together the positioned reso

comprising a power supply configured to provide a drive support vacuum encapsulation voltage to the outer and inner electrodes, the push-pull within the resonator cavity. Examplement comprising a phase of the drive voltage pro-

arrangement comprising a phase of the drive voltage pro-

vided to the inner electrode being about ministy degrees out
 $\frac{1}{2}$ 18, further comprising:

engaging of phase with the drive voltage provided to the outer electrode.

the micro-shell resonator comprises a dielectric micro-shell
spaced from and adjacent to one or both of an exterior
spaced from and adjacent to one or both of an exterior resonator, the lid-integrated electrode being configured to $\frac{45}{45}$ spaced from and adjacent to one or both of an exterior one or both of drive and sense the vibrational resonant mode
the micro-shell resonator the micro-shell resonator. using an electric gradient force.

14 The micro shell resonator system of claim 10 further 22. The method of micro-resonator fabrication of claim

comprising a spacer between the lid and the substrate, the 21, wherein the integral mechanical alignment system com-
prises an alignment key on a pre-loaded beam integral with spacer having a bonding layer to provide a seal between the $50⁵⁰$ prises an alignment key on a pre-loaded beam integral with spacer and one or both of the lid and the substrate, wherein ^{or one} of the resonator base and the resonator ind and a
the soal focilitates manteining a vecuum within the resonator corresponding alignment notch integral w the seal facilitates maintaining a vacuum within the resonator cavity.

the micro-shell resonator comprise a dielectric cylinder 55 of one or both the resonator has die resonator base, and
having a closed first and and an open second and the wherein engaging the integral mechanical alignment s having a closed first end and an open second end, the ⁵⁵ wherein engaging the integral mechanical mechanical mechanical mechanical mechanical mechanical mechanical mechanical alignment system. micro-shell resonator being attached to the resonator base at comprises:
the algoed and the lid integrated electrode ortogling into an using the out-of-plane flex of the pre-loaded beam to the closed end, the lid-integrated electrode extending into an using the out-of-plane flex of the pre-toaded beam to
interior of the prices of the prices beall reconstant the open and engage the alignment key in the alignm

16. The micro-shell resonator system of claim 10, further $\frac{1}{60}$ flexing the pre-loaded beam into the plane of the resonator magnitude complete interval to the resonator comprising a mechanical alignment system integral to the flexing the pre-loaded beam into the plane of the resonator
id or base to facilitate the positioning of the lidsubstrate and the lid, the integral mechanical alignment lid or base to facilitate the positioning of the lid-
integrated electrodes relative to the micro-shell resosystem being configured to establish the sidewall-adjacent integrated electrodes relative to the micro - shell resolution of the lid integrated electrodes relative to the micro - shell resolution of the lid position of the lid-integrated electrode with respect to microshell resonator. SINCH resonator.

base and the resonator lid, wherein the active mechanical 17. The micro-shell resonator system of claim 16, wherein alignment is configured to establish and maintain the spaced the integral mechanical alignment system comp respect to the vertical side of the MEMS resonator.
By The migral with a respective of claim 8, wherein the integral is integral with a respective other of the substrate and the lid, 9. The micro-resonator of claim 8, wherein the integral $\frac{1}{10}$ integral with a respective other of the substrate and the lid, the pre-loaded beam having an out-of-plane flex relative to

-
-
- nator base to nator base to not be the resonator base to nator base to nator base to nator base to have the surface of the resonator lid facing the surface **have the surface of the resonator surface 10 . A micro-shell resonator system comprising:** The resonator base; and σ is the resonator base; and
	- 20 resonator cavity, the micro-shell resonator being con-
20 and to the positioned resonator in a
5 and to the micro-shell resonator in a figured to exhibit a vibrational resonant mode; and tor base to enclose the micro-shell resonator in a
resonator cavity formed by the resonator lid and base.

into the resonator cavity adjacent to and spaced from a
claim 18, wherein the micro-shell resonator comprises a
alim 18, wherein the micro-shell resonator comprises a sidewall of the micro-shell resonator, wherein the lid-
integrated postposition of 25 dielectric cylinder having a closed end adjacent to the integrated electrode is configured to one or more of dielectric cylinder having a closed end adjacent to the
drive conce and tupe the vibrational reconomic mode of resonator base surface and an opposite open end, and drive, sense and tune the vibrational resonant mode of
the micro-shell resonator.
the micro-shell resonator. 11. The micro-shell resonator system of claim 10, wherein electrode and an inner electrode with respect to the exterior the lid-
the lid-integrated electrode comprises both an outer elec-
 $\frac{1}{20}$.

the vibrational resonant mode in a push-pull arrangement. $\frac{135}{35}$ iid and resonator base comprises forming a hermetic seal to 12. The micro-shell resonator system of claim 11, further ³⁵ lid and resonator base comprises forming a nermetic seal to resonator support vacuum encapsulation of the micro-shell resonator

align together the positioned resonator lid and resonator base before affixing together. 13. The micro-shell resonator system of claim 10, wherein base before a fixing together, wherein aligning together comprises positioning the lid-integrated electrodes

14. The micro-shell resonator system of claim 10, further 22. The method of micro-resonator fabrication of claim $\frac{22}{1}$, wherein the integral mechanical alignment system comother of the resonator base and the resonator lid, the pre-loaded beam having an out-of-plane flex relative to a plane 15. The micro-shell resonator system of claim 10, wherein loaded beam having an out-or-plane flex relative to a plane of $\frac{1}{2}$ of one or both the resonator lid and the resonator base, and

- interior of the micro-shell resonator at the open end.
 16. The micro-shell resonator ay the alignment compared to the alignment notation of claim 10. further align together the resonator lid and base; and
	-